

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Previously Presented) A surface protecting adhesive film for a semiconductor wafer wherein an acrylic adhesive layer having a storage elastic modulus from 1×10^5 Pa to 1×10^7 Pa at 150 °C, an adhesive force from 5g/25mm to 500g/25mm in regard to an SUS304-BA plate whereby the acrylic adhesive layer can be peeled away from a semiconductor wafer surface and a thickness of from 3 to 100 μ m is formed on both of a surface and back surface of a base film having a melting point of at least 200°C and a thickness of 10 to 200 μ m.
2. (Original) The surface protecting adhesive film for a semiconductor wafer according to claim 1, wherein the base film comprises at least one resin film selected from a group consisting of a polyethylene terephthalate, a polyethylene naphthalate, a polyphenylene sulfide and a polyimide.
3. (Currently Amended) A protecting method for a semiconductor wafer in a step of processing a non-circuit-formed surface of a semiconductor wafer comprising a first step of fixing a circuit-formed surface of the semiconductor wafer to a substrate supporting the semiconductor wafer via a surface protecting adhesive film for the semiconductor wafer having an adhesive layer on both a surface and a back

surface of a base film, a second step of fixing a non-circuit-formed surface of the semiconductor wafer on a semiconductor wafer grinding machine via the substrate and mechanically grinding the non-circuit-formed surface of the semiconductor wafer, and a third step of removing a damaged layer generated on the non-circuit-formed surface of the semiconductor wafer in sequence, wherein ~~the adhesive layer of the surface protecting adhesive film has a storage elastic modulus from 1×10^5 Pa to 1×10^7 Pa at 150 °C and a thickness of from 3 to 100 μm and is formed on both of a surface and back surface of a base film having a melting point of at least 200°C and a thickness of 10 to 200 μm~~ the adhesive layer of the surface protecting adhesive film according to claim 1 is used as the surface protecting adhesive film for the semiconductor wafer.

4. (Original) The protecting method for the semiconductor wafer according to claim 3, wherein the third step comprises at least one step selected from a wet etching step, a plasma etching step and a polishing step.